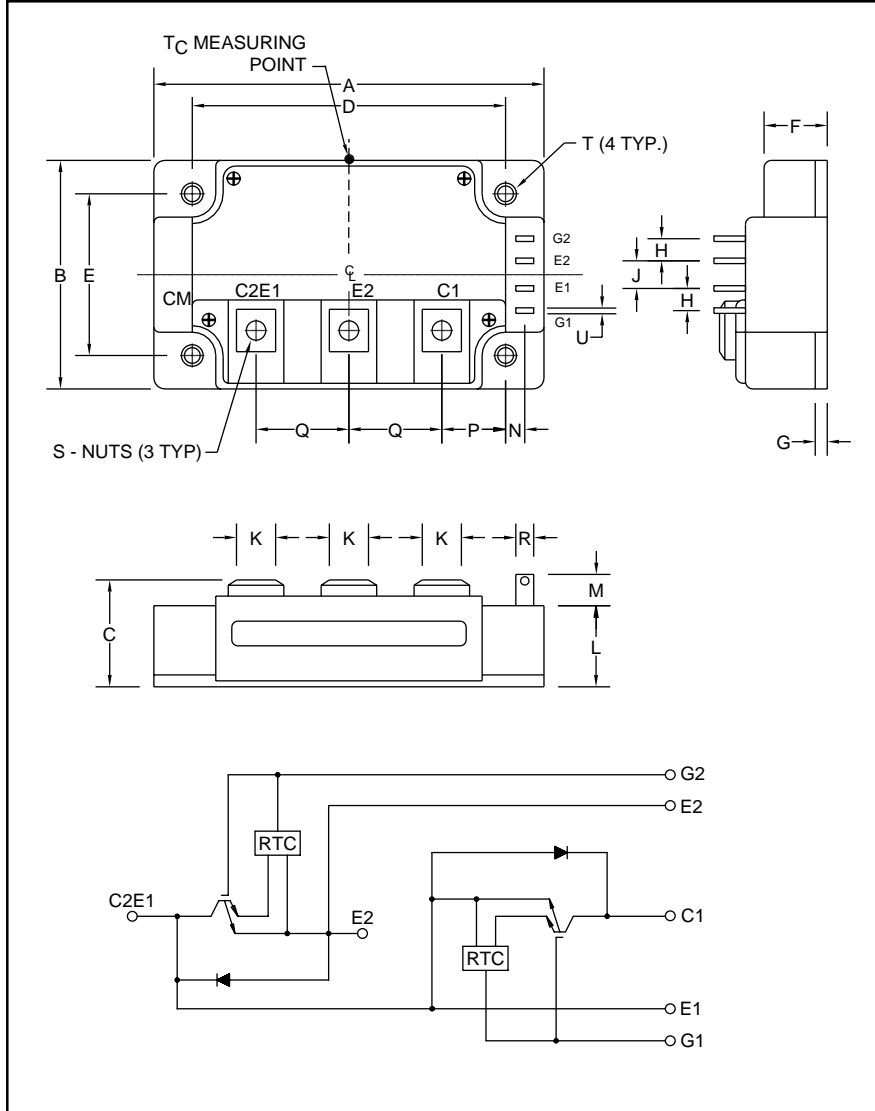


Trench Gate Design Dual IGBTMOD™ 200 Amperes/1200 Volts



Outline Drawing and Circuit Diagram

| Dimensions | Inches | Millimeters |
|------------|------------------|----------------|
| A | 4.25 | 108.0 |
| B | 2.44 | 62.0 |
| C | 1.14 +0.04/-0.02 | 29.0 +1.0/-0.5 |
| D | 3.66±0.01 | 93.0±0.25 |
| E | 1.88±0.01 | 48.0±0.25 |
| F | 0.67 | 17.0 |
| G | 0.16 | 4.0 |
| H | 0.24 | 6.0 |
| J | 0.59 | 15.0 |
| K | 0.55 | 14.0 |

| Dimensions | Inches | Millimeters |
|------------|--------|-------------|
| L | 0.87 | 22.0 |
| M | 0.33 | 8.5 |
| N | 0.10 | 2.5 |
| P | 0.85 | 21.5 |
| Q | 0.98 | 25.0 |
| R | 0.11 | 2.8 |
| S | M6 | M6 |
| T | M6.5 | M6.5 |
| U | 0.002 | 0.05 |



Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of two IGBT Transistors in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- Low Drive Power
- Low $V_{CE(sat)}$
- Discrete Super-Fast Recovery Free-Wheel Diode
- Isolated Baseplate for Easy Heat Sinking

Applications:

- AC Motor Control
- UPS
- Battery Powered Supplies

Ordering Information:

Example: Select the complete module number you desire from the table - i.e. CM200DU-24F is a 1200V (V_{CES}), 200 Ampere Dual IGBTMOD™ Power Module.

| Type | Current Rating Amperes | V_{CES} Volts (x 50) |
|------|------------------------|------------------------|
| CM | 200 | 24 |



Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (724) 925-7272

CM200DU-24F
Trench Gate Design Dual IGBTMOD™
 200 Amperes/1200 Volts

Absolute Maximum Ratings, $T_j = 25\text{ °C}$ unless otherwise specified

| Ratings | Symbol | CM200DU-24F | Units |
|---|-----------|-------------|---------|
| Junction Temperature | T_j | -40 to 150 | °C |
| Storage Temperature | T_{stg} | -40 to 125 | °C |
| Collector-Emitter Voltage (G-E SHORT) | V_{CES} | 1200 | Volts |
| Gate-Emitter Voltage (C-E SHORT) | V_{GES} | ±20 | Volts |
| Collector Current ($T_c = 25\text{ °C}$) | I_C | 200 | Amperes |
| Peak Collector Current ($T_j \leq 150\text{ °C}$) | I_{CM} | 400* | Amperes |
| Emitter Current** ($T_c = 25\text{ °C}$) | I_E | 200 | Amperes |
| Peak Emitter Current** | I_{EM} | 400* | Amperes |
| Maximum Collector Dissipation ($T_c = 25\text{ °C}$) | P_c | 830 | Watts |
| Mounting Torque, M6 Main Terminal | – | 40 | in-lb |
| Mounting Torque, M6 Mounting | – | 40 | in-lb |
| Weight | – | 400 | Grams |
| Isolation Voltage (Main Terminal to Baseplate, AC 1 min.) | V_{iso} | 2500 | Volts |

Static Electrical Characteristics, $T_j = 25\text{ °C}$ unless otherwise specified

| Characteristics | Symbol | Test Conditions | Min. | Typ. | Max. | Units |
|--------------------------------------|---------------|---|------|------|------|-------|
| Collector-Cutoff Current | I_{CES} | $V_{CE} = V_{CES}, V_{GE} = 0V$ | – | – | 1 | mA |
| Gate Leakage Voltage | I_{GES} | $V_{GE} = V_{GES}, V_{CE} = 0V$ | – | – | 40 | μA |
| Gate-Emitter Threshold Voltage | $V_{GE(th)}$ | $I_C = 20mA, V_{CE} = 10V$ | 5 | 6 | 7 | Volts |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C = 200A, V_{GE} = 15V, T_j = 25\text{ °C}$ | – | 1.8 | 2.4 | Volts |
| | | $I_C = 200A, V_{GE} = 15V, T_j = 125\text{ °C}$ | – | 1.9 | – | Volts |
| Total Gate Charge | Q_G | $V_{CC} = 600V, I_C = 200A, V_{GE} = 15V$ | – | 2200 | – | nC |
| Emitter-Collector Voltage** | V_{EC} | $I_E = 200A, V_{GE} = 0V$ | – | – | 3.2 | Volts |

* Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.

** Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).



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CM200DU-24F
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Dynamic Electrical Characteristics, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

| Characteristics | Symbol | Test Conditions | Min. | Typ. | Max. | Units | |
|---------------------------------|---------------------|-----------------------------|------------------------------|------|------|-------|---------------|
| Input Capacitance | C_{ies} | | – | – | 78 | nf | |
| Output Capacitance | C_{oes} | $V_{CE} = 10V, V_{GE} = 0V$ | – | – | 3.4 | nf | |
| Reverse Transfer Capacitance | C_{res} | | – | – | 2 | nf | |
| Inductive | Turn-on Delay Time | $t_{d(on)}$ | $V_{CC} = 600V, I_C = 200A,$ | – | – | 300 | ns |
| Load | Rise Time | t_r | $V_{GE1} = V_{GE2} = 15V,$ | – | – | 80 | ns |
| Switch | Turn-off Delay Time | $t_{d(off)}$ | $R_G = 1.6\Omega,$ | – | – | 500 | ns |
| Times | Fall Time | t_f | Inductive Load | – | – | 300 | ns |
| Diode Reverse Recovery Time** | t_{rr} | Switching Operation | | – | – | 200 | ns |
| Diode Reverse Recovery Charge** | Q_{rr} | $I_E = 200A$ | | – | 12.2 | – | μC |

Thermal and Mechanical Characteristics, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

| Characteristics | Symbol | Test Conditions | Min. | Typ. | Max. | Units |
|--------------------------------------|-----------------|--|------|-------|------|--------------------|
| Thermal Resistance, Junction to Case | $R_{th(j-c)Q}$ | Per IGBT 1/2 Module, T_C Reference Point per Outline Drawing | – | | 0.15 | $^\circ\text{C/W}$ |
| Thermal Resistance, Junction to Case | $R_{th(j-c)D}$ | Per FWDi 1/2 Module, T_C Reference Point per Outline Drawing | – | – | 0.18 | $^\circ\text{C/W}$ |
| Thermal Resistance, Junction to Case | $R_{th(j-c)'Q}$ | Per IGBT 1/2 Module, T_C Reference Point Under Chip | – | 0.08 | | $^\circ\text{C/W}$ |
| Contact Thermal Resistance | $R_{th(c-f)}$ | Per Module, Thermal Grease Applied | – | 0.020 | – | $^\circ\text{C/W}$ |

** Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).